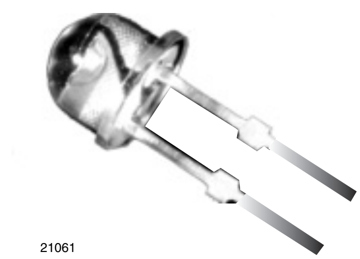
High Speed Infrared Emitting Diode, 870 nm, GaAlAs Double Hetero

Description

TSFF5510 is an infrared, 870 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted, plastic package.



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Features

- Package type: leaded
- Dimensions: T-1¾ (∅ 5 mm)
- Peak wavelength: λ_p = 870 nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: φ = ± 38°
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth
- Good spectral matching to Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Pb-free

e2

Applications

- Infrared video data transmission between camcorder and TV set
- Free air data transmission systems with high modulation frequencies or high data transmission

Product Summary

Component	Symbol	Value	Unit
TSFF5510	ϕ_e	55	mW
	I_e	32	mW/sr
	t_r, t_f	15	ns
	φ	± 38	deg
	λ_p	870	nm

Ordering Information

Ordering code	Packing	Remarks
TSFF5510	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk

Note:
MOQ: minimum order quantity

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	1	A
Power dissipation		P_V	170	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	250	K/W

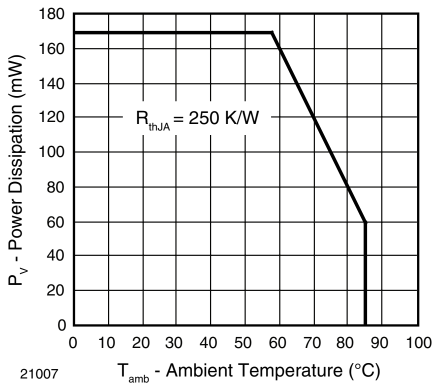


Figure 1. Power Dissipation Limit vs. Ambient Temperature

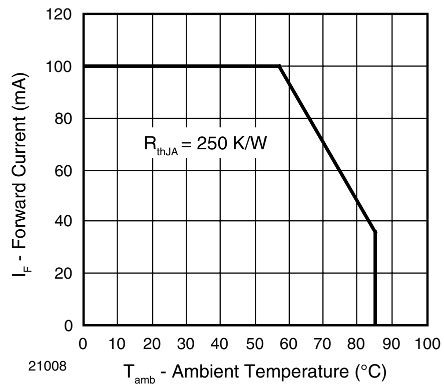


Figure 2. Forward Current Limit vs. Ambient Temperature

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F	1.3	1.45	1.7	V
	I_F = 450 mA, t_p = 100 µs	V_F	1.5	1.75	2.1	V
	I_F = 1 A, t_p = 100 µs	V_F		2.1		V
Temperature coefficient of V_F	I_F = 1 mA	TK_{VF}		- 1.8		mV/K
Reverse current	V_R = 5 V	I_R			10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		110		pF

Optical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Typ.	Max.	Unit
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e		32		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e	44	55	89	mW
	I_F = 450 mA, t_p = 100 µs	ϕ_e	200	247	400	mW
	I_F = 1 A, t_p = 100 µs	ϕ_e		550		mW
Temperature coefficient of ϕ_e	I_F = 100 mA	$TK\phi_e$		- 0.35		%/K
Angle of half intensity		φ		± 38		deg
Peak wavelength	I_F = 100 mA	λ_p		870		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		55		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.25		nm/K
Rise time	I_F = 100 mA	t_r		15		ns
Fall time	I_F = 100 mA	t_f		15		ns
Cut-off frequency	I_{DC} = 70 mA, I_{AC} = 30 mA pp	f_c		23		MHz

Basic Characteristics

T_{amb} = 25 °C, unless otherwise specified

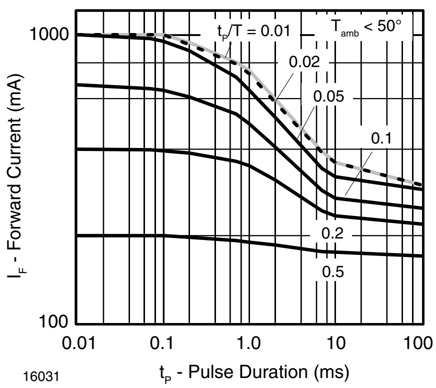


Figure 3. Pulse Forward Current vs. Pulse Duration

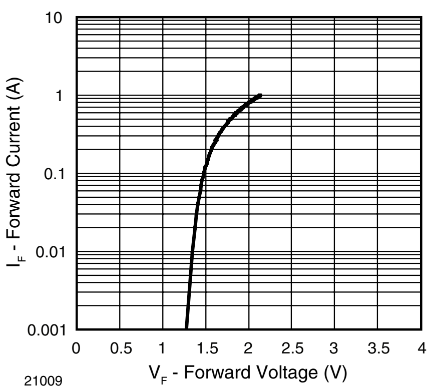


Figure 4. Forward Current vs. Forward Voltage

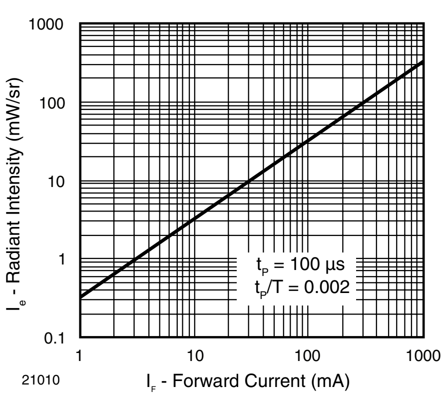


Figure 5. Radiant Intensity vs. Forward Current

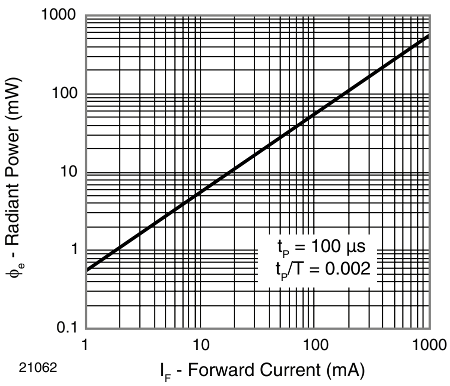


Figure 6. Radiant Power vs. Forward Current

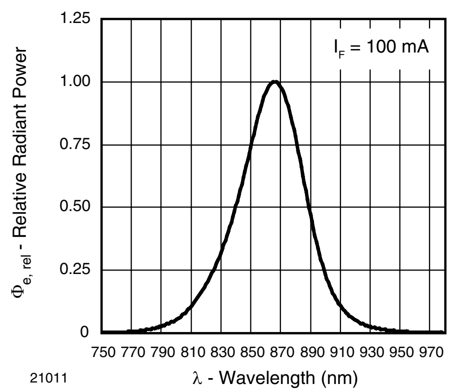


Figure 7. Relative Radiant Power vs. Wavelength

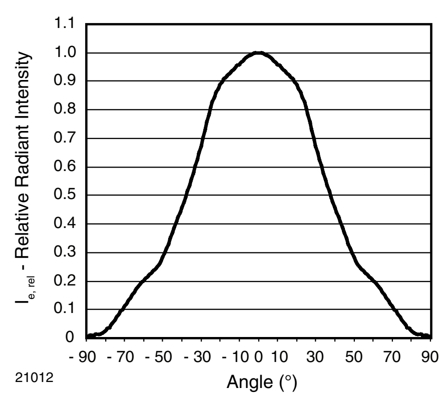
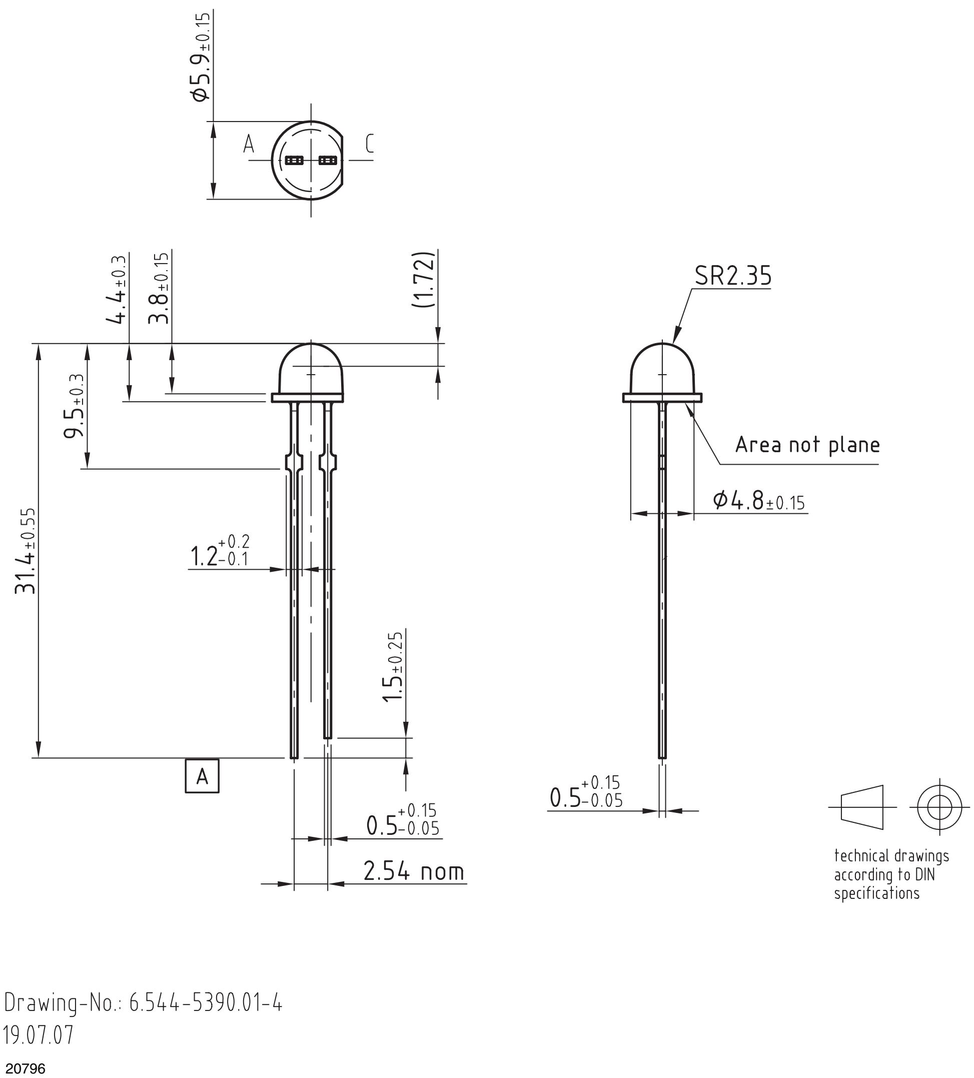


Figure 8. Relative Radiant Intensity vs. Angular Displacement

Package Dimensions in millimeters



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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